

Dr. [unclear] [unclear]
a basic atmosphere.

13. A chemical-mechanical polishing process according to claim 12, wherein the particles of boehmite are formed by dipping of particles of Al in hot water.

14. A chemical-mechanical polishing process according to claim 13, wherein said hot water is added with sodium aluminate.

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16. (amended) A chemical-mechanical polishing process for planarizing one or more films formed on a substrate, wherein said thin films are subjected to chemical-mechanical polishing using a slurry containing abrasive particles [containing] consisting essentially of boehmite, and the residual slurry and contamination are removed by spin cleaning.

17. A chemical-mechanical polishing process according to claim 16, wherein said spin cleaning is performed using chemicals comprising a solution containing NH_4 , H_2O_2 , and H_2O , followed by a hydrofluoric acid solution.

18. A chemical-mechanical polishing process according to claim 17, wherein after spin cleaning using said chemicals, said substrate is rinsed with pure water.

19. A chemical-mechanical polishing process according to claim 16, wherein the abrasive particles of boehmite are formed by dipping of particles of Al in a hot water.

20. A chemical-mechanical polishing process according to claim 19, wherein said hot water is added with sodium aluminate.

21. (amended) A chemical-mechanical polishing process for planarizing one or more of thin films formed on a substrate, wherein said chemical-mechanical polishing is performed using a basic slurry containing abrasive particles made of a material higher in hardness than SiO₂.

22. (new) A polishing process which comprises the steps of:

forming a slurry containing abrasive boehmite particles by dipping particles of aluminum in heated water; and planarizing at least one film formed on a substrate by employing a chemical-mechanical polishing process using said slurry.

23. (new) A polishing process according to claim 22, wherein said step of forming a slurry includes adding sodium

aluminate to said heated water.

24. (new) A polishing process according to claim 22, wherein said heated water is about 80 °C.

25. (new) A polishing process according to claim 22, wherein said chemical-mechanical polishing process is performed in a basic atmosphere.

26. (new) A polishing process according to claim 25, wherein said boehmite particles are suspended in a solution containing KOH, water, and an alcohol.

27. (new) A polishing process according to claim 22, wherein said film is an interlayer dielectric film.

REMARKS

This is a full and timely response to the non-final Official Action mailed April 29, 1999. Reexamination and reconsideration in light of the above amendments and the following remarks are courteously requested.

By the foregoing amendment, claims 12 and 16 have been amended. Additionally, new claims 22 to 27 have been added. Thus, claims 12 to 14, and 16 to 27 are currently pending for the Examiner's consideration.